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Silicon Carbide Schottky Diode 1200 V, 20 A



Description

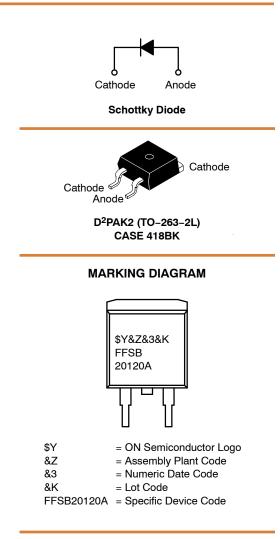
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 200 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- AEC-Q101 qualified

Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSB20120A-F085

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter		Ratings	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage		1200	V	
E _{AS}	Single Pulse Avalanche Energy	(Note 1)	200	mJ	
I _F	Continuous Rectified Forward Current @ T _C < 157°C		20	А	
	Continuous Rectified Forward Current @ T _C < 135°C		32	1	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1190	А	
		T _C = 150°C, 10 μs	990	1	
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	135	А	
I _{F, RM}	Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	74	А	
Ptot	Power Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$	333	W	
		T _C = 150°C	55	W	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.45	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping [†]	
FFSB20120A-F085	FFSB20120A	D2PAK	800 Units/ Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Unit
V _F	Forward Voltage	$I_{\rm F}$ = 20 A, $T_{\rm C}$ = 25°C	-	1.45	1.75	V
		I _F = 20 A, T _C = 125°C	-	1.7	2	
		I _F = 20 A, T _C = 175°C	-	2	2.4	
I _R	Reverse Current	$V_{R} = 1200 \text{ V}, \text{ T}_{C} = 25^{\circ}\text{C}$	-	-	200	μA
		$V_{\rm R}$ = 1200 V, $T_{\rm C}$ = 125°C	-	-	300	
		$V_{R} = 1200 \text{ V}, \text{ T}_{C} = 175^{\circ}\text{C}$	-	-	400	
Q _C	Total Capacitive Charge	V = 800 V	-	120	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	1220	-	pF
		V _R = 400 V, f = 100 kHz	-	111	-	
		V _R = 800 V, f = 100 kHz	-	88	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. E_{AS} of 200 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 29 A, V = 50 V.

FFSB20120A-F085

TYPICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

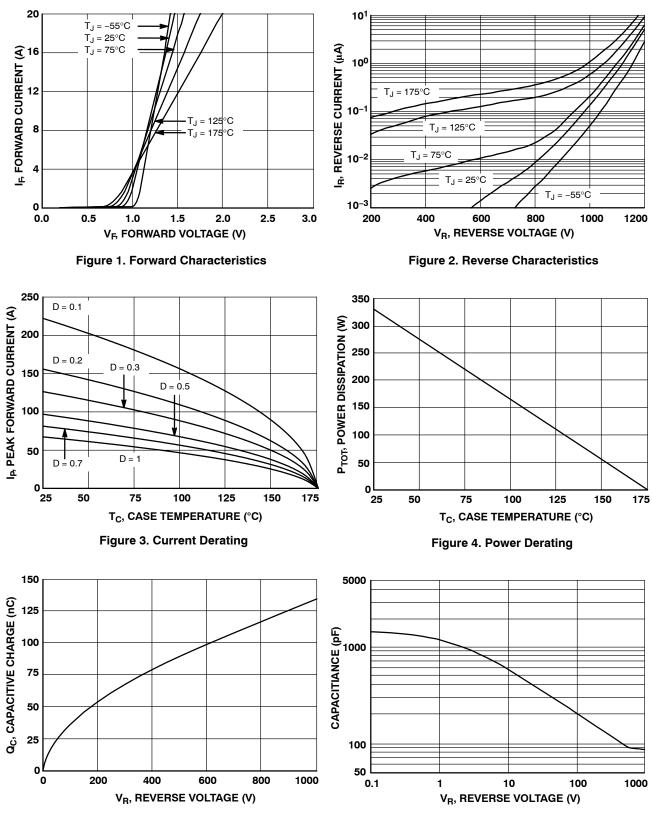
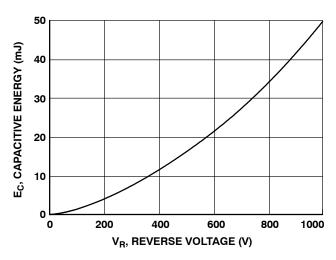


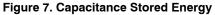
Figure 5. Capacitive Charge vs. Reverse Voltage

Figure 6. Capacitive Charge vs. Reverse Voltage

FFSB20120A-F085

TYPICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted) (continued)





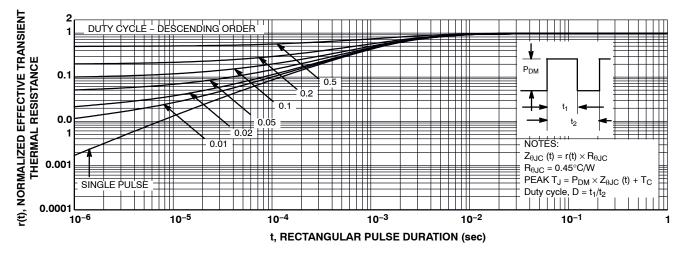
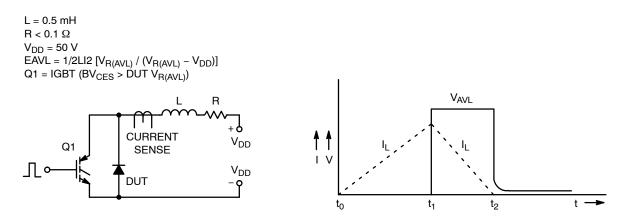


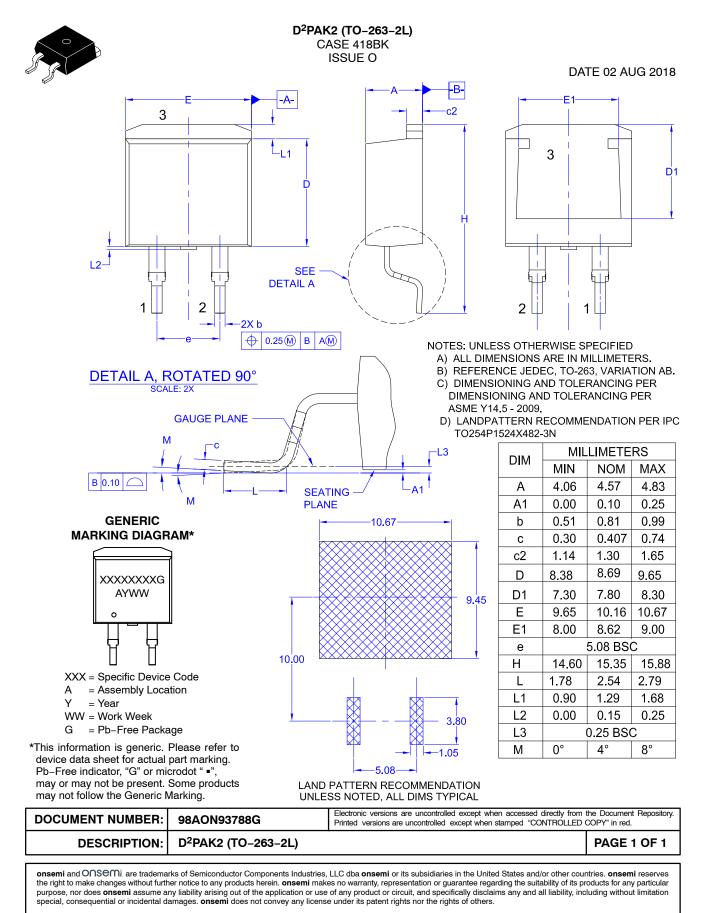
Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS





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